

NTMFD4902NF

Dual N-Channel Power MOSFET with Integrated Schottky

30 V, High Side 18 A / Low Side 23 A, Dual N-Channel SO8FL

Features

- Co-Packaged Power Stage Solution to Minimize Board Space
- Low Side MOSFET with Integrated Schottky
- Minimized Parasitic Inductances
- Optimized Devices to Reduce Power Losses
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

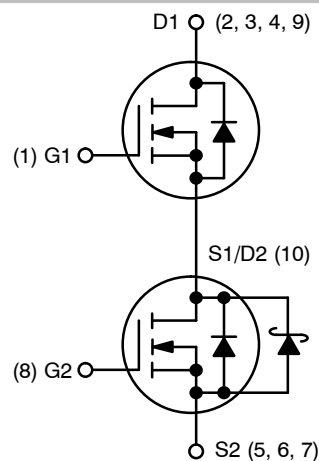
- DC-DC Converters
- System Voltage Rails
- Point of Load



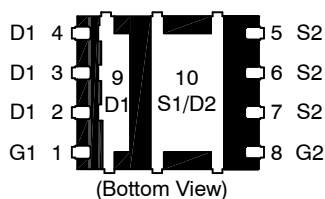
ON Semiconductor®

<http://onsemi.com>

$V_{(BR)DSS}$	$R_{DS(ON)} \text{ MAX}$	$I_D \text{ MAX}$
Q1 Top FET 30 V	6.5 m Ω @ 10 V	18 A
	10 m Ω @ 4.5 V	
Q2 Bottom FET 30 V	4.1 m Ω @ 10 V	23 A
	6.2 m Ω @ 4.5 V	



PIN CONNECTIONS



MARKING DIAGRAM



4902NF = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
ZZ = Lot Traceability

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

NTMFD4902NF

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter				Symbol	Value	Unit	
Drain-to-Source Voltage			Q1	V _{DSS}	30	V	
Drain-to-Source Voltage			Q2				
Gate-to-Source Voltage			Q1	V _{GS}	±20	V	
Gate-to-Source Voltage			Q2				
Continuous Drain Current R _{θJA} (Note 1)	Steady State	T _A = 25°C	Q1	I _D	13.5	A	
		T _A = 85°C			9.7		
		T _A = 25°C	Q2		17.5		
		T _A = 85°C			12.6		
Power Dissipation R _{θJA} (Note 1)		T _A = 25°C	Q1	P _D	1.90	W	
			Q2		1.99		
Continuous Drain Current R _{θJA} ≤ 10 s (Note 1)		T _A = 25°C	Q1	I _D	18.2	A	
		T _A = 85°C			13.1		
		T _A = 25°C	Q2		23		
		T _A = 85°C			16.6		
Power Dissipation R _{θJA} ≤ 10 s (Note 1)		T _A = 25°C	Q1	P _D	3.45	W	
			Q2		3.45		
Continuous Drain Current R _{θJA} (Note 2)		T _A = 25°C	Q1	I _D	10.3	A	
		T _A = 85°C			7.4		
		T _A = 25°C	Q2		13.3		
		T _A = 85°C			9.6		
Power Dissipation R _{θJA} (Note 2)		T _A = 25 °C	Q1	P _D	1.10	W	
			Q2		1.16		
Pulsed Drain Current		TA = 25°C tp = 10 μs	Q1	I _{DM}	60	A	
			Q2		80		
Operating Junction and Storage Temperature			Q1	T _J , T _{STG}	-55 to +150	°C	
			Q2				
Source Current (Body Diode)			Q1	I _S	3.4	A	
			Q2		4.9		
Drain to Source dV/dt				dV/dt	6.0	V/ns	
Single Pulse Drain-to-Source Avalanche Energy (T _J = 25C, V _{DD} = 50 V, V _{GS} = 10 V, I _L = XX A _{pk} , L = 0.1 mH, R _G = 25 Ω)		24 A	Q1	EAS	28.8	mJ	
		27 A	Q2	EAS	36.5		
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)				T _L	260	°C	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Surface-mounted on FR4 board using 1 sq-in pad, 2 oz Cu.
2. Surface-mounted on FR4 board using the minimum recommended pad size of 100 mm².

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	FET	Symbol	Value	Unit
Junction-to-Ambient – Steady State (Note 3)	Q1	$R_{\theta JA}$	65.9	$^{\circ}\text{C/W}$
	Q2		62.8	
Junction-to-Ambient – Steady State (Note 4)	Q1	$R_{\theta JA}$	113.2	
	Q2		108	
Junction-to-Ambient – ($t \leq 10$ s) (Note 3)	Q1	$R_{\theta JA}$	36.2	
	Q2		36.2	

3. Surface-mounted on FR4 board using 1 sq-in pad, 2 oz Cu.

4. Surface-mounted on FR4 board using the minimum recommended pad size of 100 mm².

ELECTRICAL CHARACTERISTICS ($T_J = 25^{\circ}\text{C}$ unless otherwise specified)

Parameter	FET	Symbol	Test Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS							
Drain-to-Source Break-down Voltage	Q1	$V_{(BR)DSS}$	$V_{GS} = 0$ V, $I_D = 250$ μA	30			V
	Q2		$V_{GS} = 0$ V, $I_D = 1.0$ mA	30			
Drain-to-Source Break-down Voltage Temperature Coefficient	Q1	$V_{(BR)DSS} / T_J$			18		mV / $^{\circ}\text{C}$
	Q2				15		
Zero Gate Voltage Drain Current	Q1	I_{DSS}	$V_{GS} = 0$ V, $V_{DS} = 24$ V	$T_J = 25^{\circ}\text{C}$		1	μA
				$T_J = 125^{\circ}\text{C}$		10	
	Q2	I_{DSS}	$V_{GS} = 0$ V, $V_{DS} = 24$ V	$T_J = 25^{\circ}\text{C}$		500	
				$T_J = 125^{\circ}\text{C}$		500	
Gate-to-Source Leakage Current	Q1	I_{GSS}	$V_{GS} = 0$ V, $V_{DS} = \pm 20$ V			± 100	nA
	Q2					± 100	

ON CHARACTERISTICS (Note 5)

Gate Threshold Voltage	Q1	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250 \mu A$		1.2		2.2	V
	Q2				1.2		2.2	
Negative Threshold Temperature Coefficient	Q1	$V_{GS(TH)} / T_J$				4.5		mV / °C
	Q2					4.0		
Drain-to-Source On Resistance	Q1	$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$	$I_D = 10 \text{ A}$		5.2	6.5	mΩ
			$V_{GS} = 4.5 \text{ V}$	$I_D = 10 \text{ A}$		8.0	10	
	Q2		$V_{GS} = 10 \text{ V}$	$I_D = 15 \text{ A}$		3.3	4.1	
			$V_{GS} = 4.5 \text{ V}$	$I_D = 15 \text{ A}$		5.0	6.2	
Forward Transconductance	Q1	g_{FS}	$V_{DS} = 1.5 \text{ V}, I_D = 10 \text{ A}$			28		S
	Q2					35		

CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	Q1	C _{ISS}	V _{GS} = 0 V, f = 1 MHz, V _{DS} = 15 V		1150		pF
	Q2				1590		
Output Capacitance	Q1	C _{OSS}			360		
	Q2				813		
Reverse Capacitance	Q1	C _{RSS}			105		
	Q2				83		

5. Pulse Test: pulse width ≤ 300 μs , duty cycle $\leq 2\%$.

6. Switching characteristics are independent of operating junction temperatures.

NTMFD4902NF

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	FET	Symbol	Test Condition	Min	Typ	Max	Unit
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CHARGES, CAPACITANCES & GATE RESISTANCE

Total Gate Charge	Q1	Q _{G(TOT)}	V _{GS} = 4.5 V, V _{DS} = 15 V; I _D = 10 A		9.7		nC
	Q2				11.5		
Threshold Gate Charge	Q1	Q _{G(TH)}			1.1		
	Q2				1.4		
Gate-to-Source Charge	Q1	Q _{GS}			3.3		
	Q2				4.2		
Gate-to-Drain Charge	Q1	Q _{GD}			3.7		
	Q2				3.4		
Total Gate Charge	Q1	Q _{G(TOT)}	V _{GS} = 10 V, V _{DS} = 15 V; I _D = 10 A		19.1		nC
	Q2				24.9		

SWITCHING CHARACTERISTICS (Note 6)

Turn-On Delay Time	Q1	$t_{d(ON)}$	$V_{GS} = 4.5\text{ V}, V_{DS} = 15\text{ V},$ $I_D = 10\text{ A}, R_G = 3.0\ \Omega$		9.0		ns
	Q2				10.5		
Rise Time	Q1	t_r			15		
	Q2				15.2		
Turn-Off Delay Time	Q1	$t_{d(OFF)}$			14		
	Q2				17.7		
Fall Time	Q1	t_f			4.0		
	Q2				4.7		

SWITCHING CHARACTERISTICS (Note 6)

Turn-On Delay Time	Q1	$t_{d(ON)}$	$V_{GS} = 10\text{ V}, V_{DS} = 15\text{ V},$ $I_D = 10\text{ A}, R_G = 3.0\ \Omega$		6.0		ns
	Q2				7.0		
Rise Time	Q1	t_r			14		
	Q2				14		
Turn-Off Delay Time	Q1	$t_{d(OFF)}$			17		
	Q2				22		
Fall Time	Q1	t_f			3.0		
	Q2				3.3		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Voltage	Q1	VSD	VGS = 0 V, IS = 3 A	TJ = 25°C		0.75	1.0	V
				TJ = 125°C		0.62		
	Q2		VGS = 0 V, IS = 2 A	TJ = 25°C		0.37	0.70	
				TJ = 125°C		0.31		

5. Pulse Test: pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.

6. Switching characteristics are independent of operating junction temperatures.

NTMFD4902NF

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	FET	Symbol	Test Condition	Min	Typ	Max	Unit
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DRAIN-SOURCE DIODE CHARACTERISTICS

Reverse Recovery Time	Q1	t_{RR}	$V_{GS} = 0\text{ V}, d_{IS}/d_t = 100\text{ A}/\mu s, I_S = 3\text{ A}$		23		ns
	Q2				24.5		
Charge Time	Q1	t_a			12		
	Q2				13		
Discharge Time	Q1	t_b			11		
	Q2				11.5		
Reverse Recovery Charge	Q1	Q_{RR}			12		nC
	Q2				24		

PACKAGE PARASITIC VALUES

Source Inductance	Q1	L _S	T _A = 25°C		0.38		nH
	Q2				0.65		
Drain Inductance	Q1	L _D			0.054		nH
	Q2				0.007		
Gate Inductance	Q1	L _G			1.5		nH
	Q2				1.5		
Gate Resistance	Q1	R _G			0.8		Ω
	Q2				0.8		

5. Pulse Test: pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

6. Switching characteristics are independent of operating junction temperatures.

ORDERING INFORMATION

Device	Package	Shipping [†]
NTMFD4902NFT1G	DFN8 (Pb-Free)	1500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

TYPICAL CHARACTERISTICS – Q1

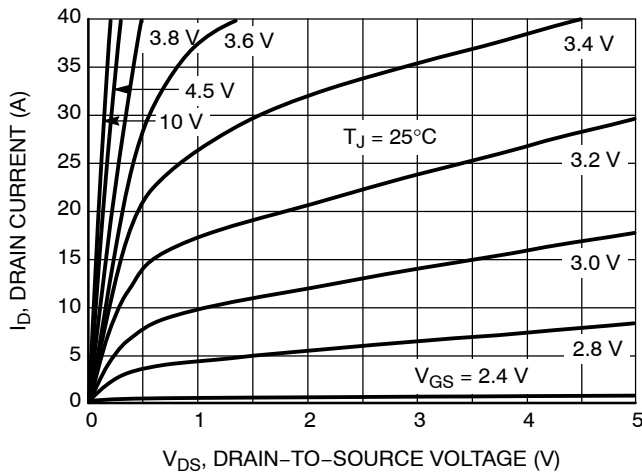


Figure 1. On-Region Characteristics

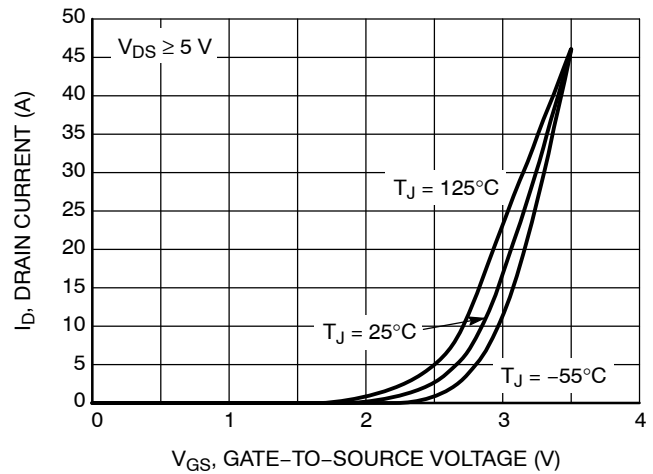


Figure 2. Transfer Characteristics

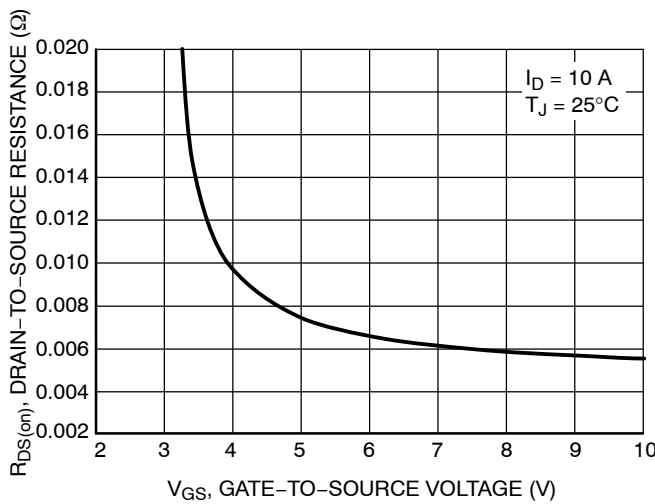


Figure 3. On-Resistance vs. Gate-to-Source Resistance

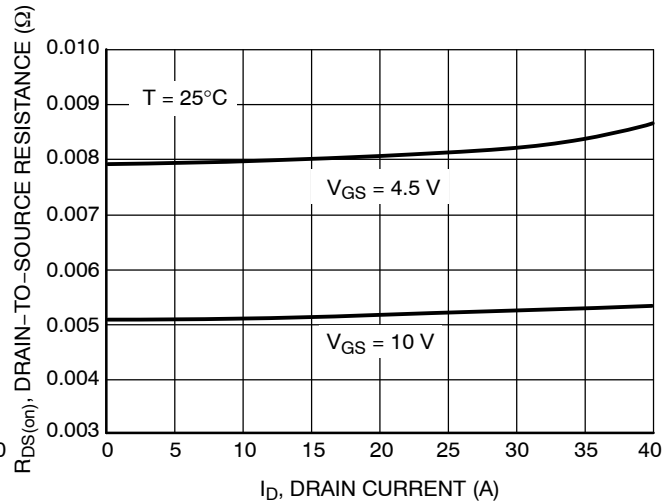


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

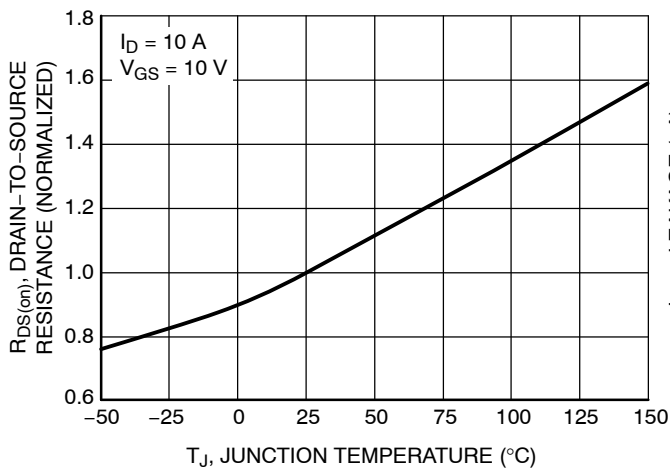


Figure 5. On-Resistance Variation with Temperature

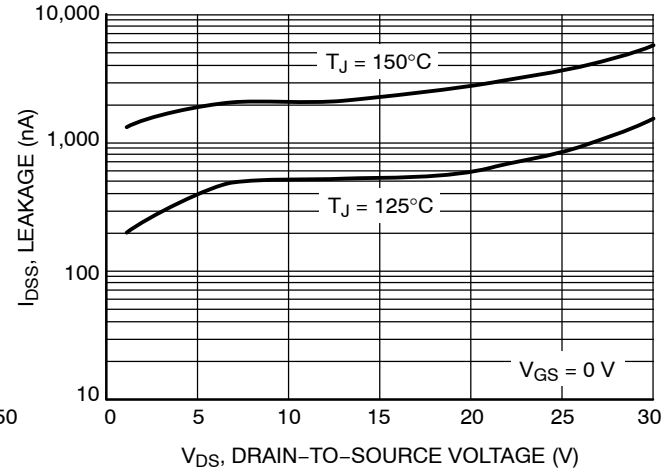


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS – Q1

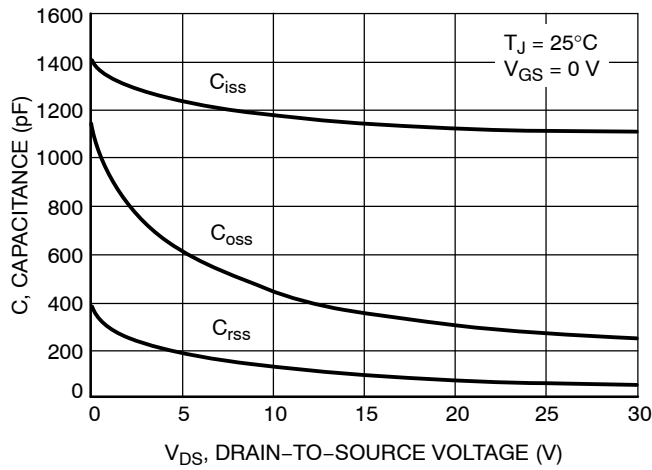


Figure 7. Capacitance Variation

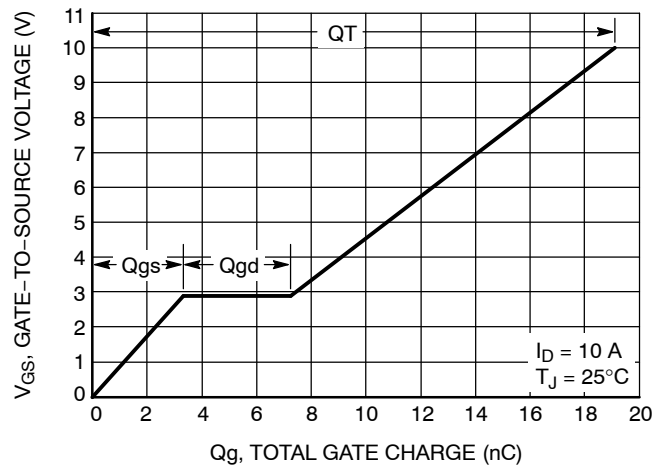


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

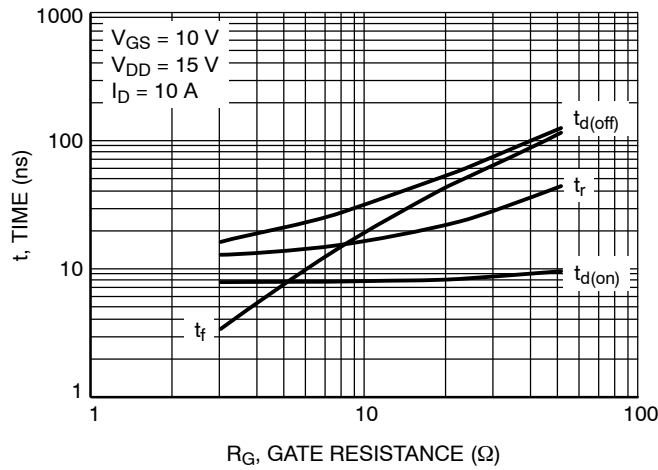


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

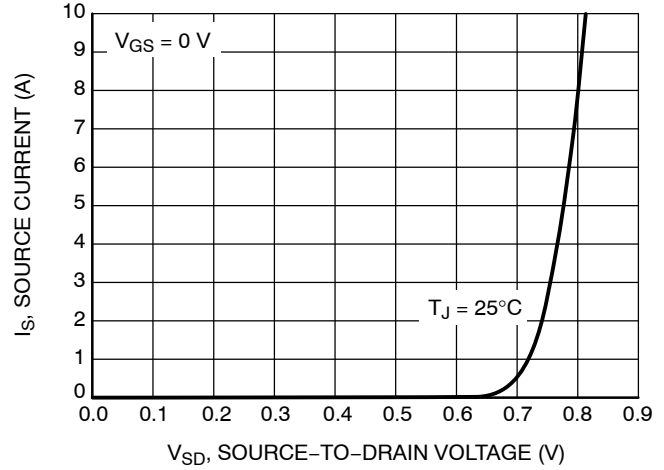


Figure 10. Diode Forward Voltage vs. Current

TYPICAL CHARACTERISTICS – Q2

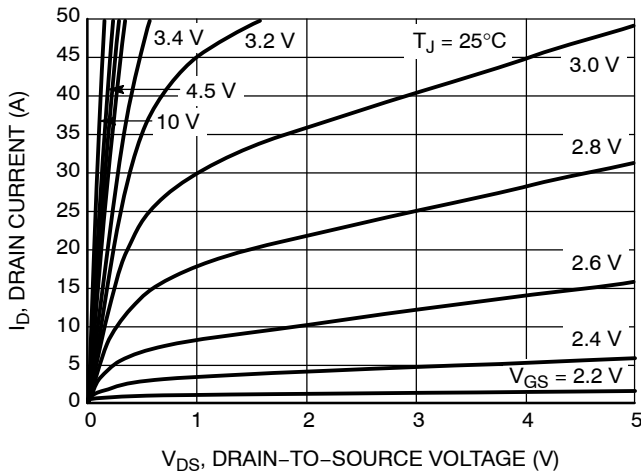


Figure 11. On-Region Characteristics

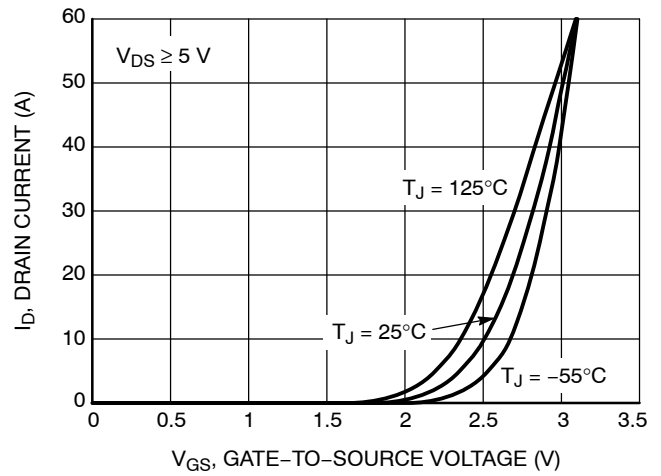


Figure 12. Transfer Characteristics

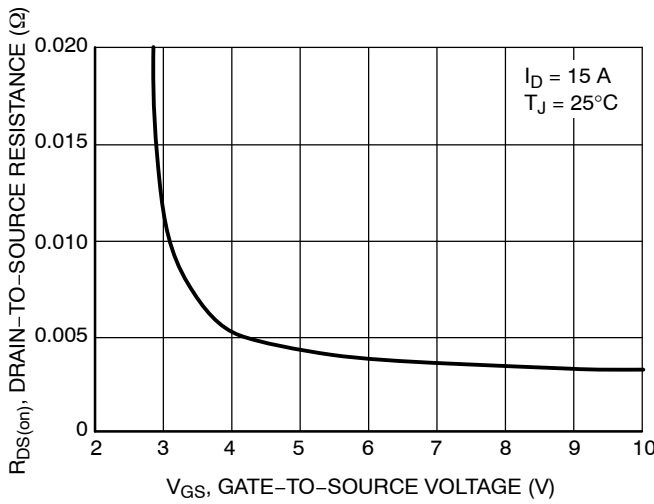


Figure 13. On-Resistance vs. Gate-to-Source Resistance

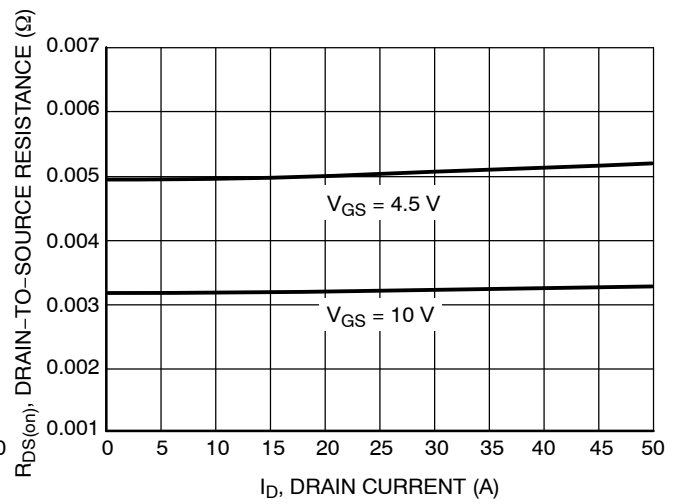


Figure 14. On-Resistance vs. Drain Current and Gate Voltage

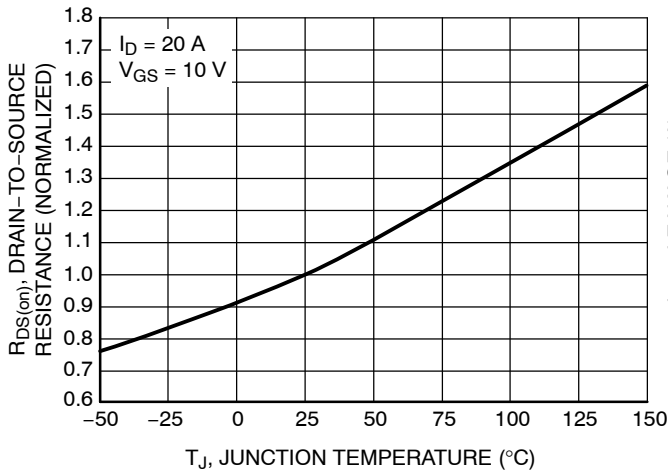


Figure 15. On-Resistance Variation with Temperature

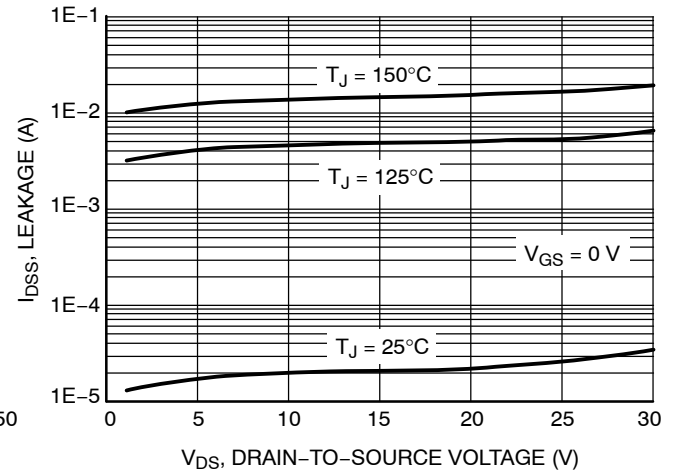


Figure 16. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS – Q2

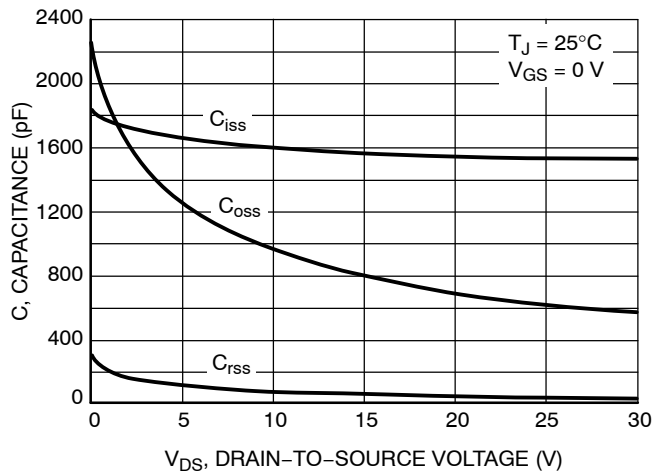


Figure 17. Capacitance Variation

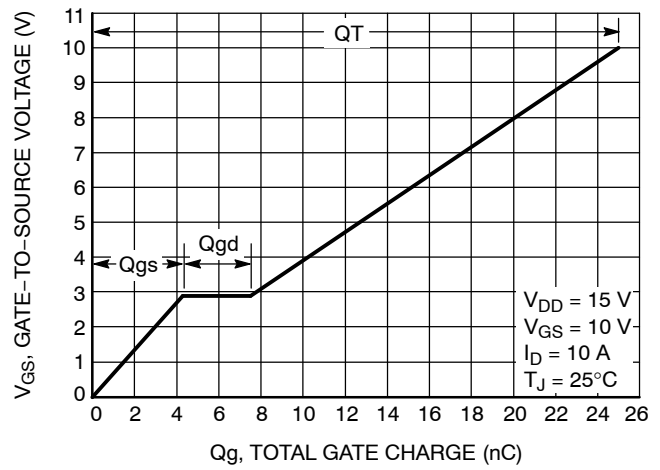


Figure 18. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

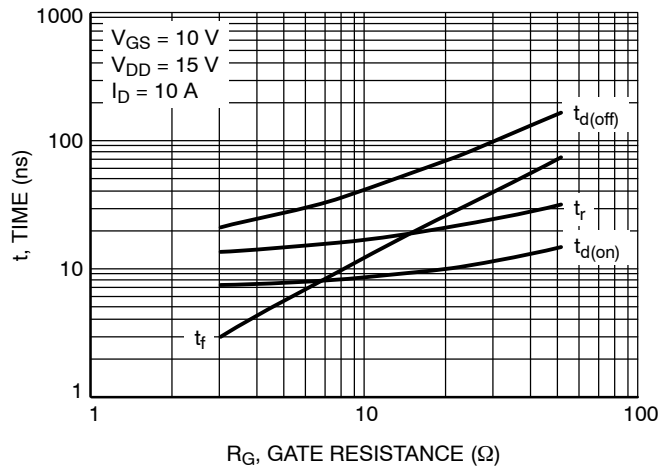


Figure 19. Resistive Switching Time Variation vs. Gate Resistance

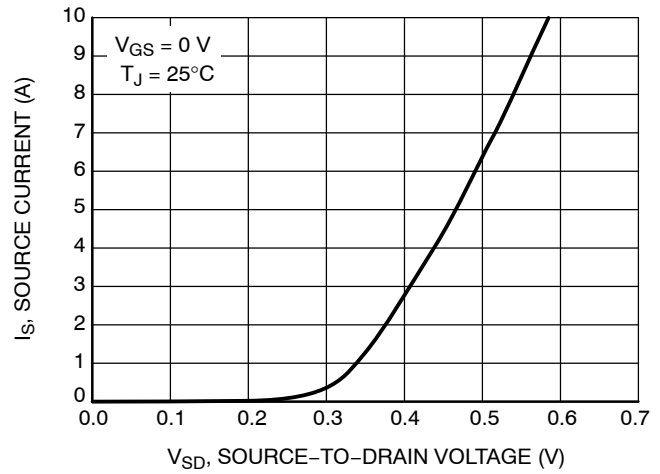
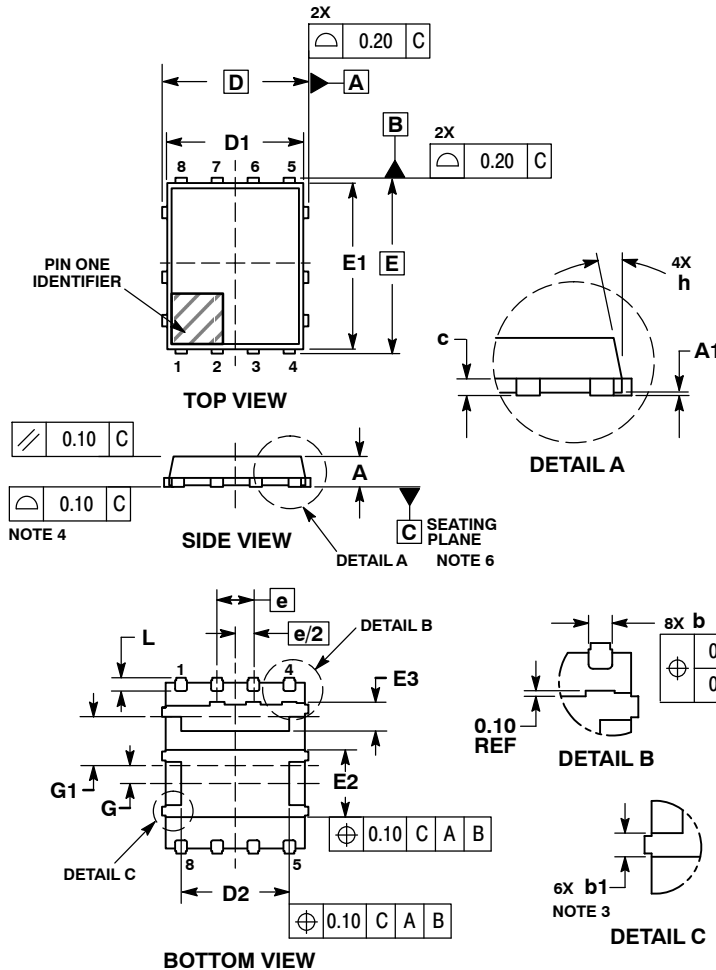


Figure 20. Diode Forward Voltage vs. Current

PACKAGE DIMENSIONS

DFN8 5x6, 1.27P Dual Flag (SO8FL–Dual–Asymmetrical)
CASE 506BX
ISSUE C

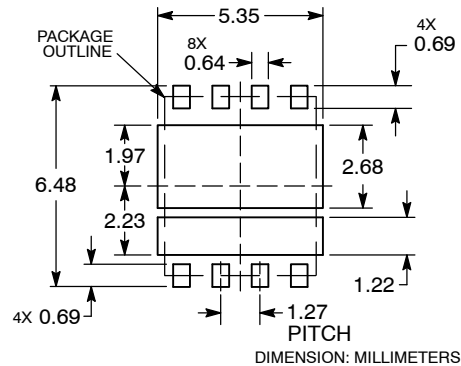


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSIONS b AND b1 APPLY TO PLATED FEATURES AND ARE MEASURED BETWEEN 0.15 AND 0.25 MM FROM TERMINAL TIPS.
4. COPLANARITY APPLIES TO THE EXPOSED PADS AS WELL AS THE TERMINALS.
5. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.
6. SEATING PLANE IS DEFINED BY THE TERMINALS. A1 IS DEFINED AS THE DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.

MILLIMETERS		
DIM	MIN	MAX
A	0.90	1.10
A1	0.00	0.05
b	0.41	0.61
b1	0.41	0.61
c	0.23	0.33
D	5.15 BSC	
D1	4.50	5.10
D2	3.50	4.22
E	6.15 BSC	
E1	5.50	6.10
E2	2.27	2.67
E3	0.82	1.22
e	1.27 BSC	
g	0.63 BSC	
G1	1.72 BSC	
h	---	12 °
L	0.35	0.55

**RECOMMENDED
SOLDERING FOOTPRINT***



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
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- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

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- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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